Triacs

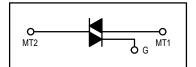
Silicon Bidirectional Triode Thyristors

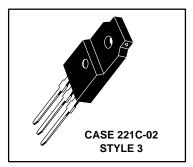
. . . designed primarily for industrial and consumer applications for full wave control of ac loads such as appliance controls, heater controls, motor controls, and other power switching applications.

- Four Mode Triggering for Drive Circuits that Source Current
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal resistance and High Heat Dissipation
- · Center Gate Geometry for Uniform Current Spreading

MAC228FP Series MAC228AFP Series

TRIACs 8 AMPERES RMS 200 thru 800 VOLTS





MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ (T _J = -40 to 110°C	VDRM		Volts
1/2 Sine Wave 50 to 60 Hz, Gate Open) MAC228-4FP, MAC228A4FP		200	
MAC228-6FP, MAC228A6FP		400	
MAC228-8FP, MAC228A8FP		600	
MAC228-10FP, MAC228A10FP		800	
On-State RMS Current ($T_C = 80^{\circ}C$) Full Cycle Sine Wave 50 to 60 Hz	IT(RMS)	8	Amps
Peak Non-repetitive Surge Current (One Full Cycle 60 Hz, T _J = 110°C)	ltsm	80	Amps
Circuit Fusing (t = 8.3 ms)	l ² t	26	A ² s
Peak Gate Current (t ≤ 2 μs)	I _{GM}	±2	Amps
Peak Gate Voltage (t ≤ 2 μs)	V _{GM}	±10	Volts
Peak Gate Power (t \leq 2 μ s)	P _{GM}	20	Watts
Average Gate Power ($T_C = 80^{\circ}C$, $t \leq 8.3 \text{ ms}$)	P _{G(AV)}	0.5	Watts
Operating Junction Temperature Range	TJ	-40 to 110	°C
Storage Temperature Range	T _{stg}	-40 to 150	°C
Mounting Torque		8	in. lb.

^{1.} V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

^{2.} The case temperature reference point for all TC measurements is a point on the center lead of the package as close as possible to the plastic body.



MAC228FP Series MAC228AFP Series

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	2.2	°C/W
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	60	°C/W

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_{C} = 25^{\circ}\text{C} \ \text{and either polarity of MT2 to MT1 voltage unless otherwise noted.})$

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current $(V_D = Rated V_{DRM}, Gate Open)$ $T_J = 25^{\circ}C$ $T_J = 110^{\circ}C$	IDRM	_	_	10 2	μA mA
Peak On-State Voltage (I _{TM} = 11 A Peak, Pulse Width ≤ 2 ms, Duty Cycle ≤ 2%)	VTM	_	_	1.8	Volts
Gate Trigger Current (Continuous dc) $ (V_D=12\ V,\ R_L=100\ \Omega) \\ MT2(+),\ G(+);\ MT2(+),\ G(-);\ MT2(-),\ G(-) \\ MT2(-),\ G(+)\ "A"\ Suffix\ Only $	^I GT		_	5 10	mA
Gate Trigger Voltage (Continuous dc) $ (V_D = 12 \text{ V}, R_L = 100 \Omega) \\ \text{MT2(+)}, G(+); \text{MT2(+)}, G(-); \text{MT2(-)}, G(-) \\ \text{MT2(-)}, G(+) "A" Suffix Only \\ (V_D = Rated V_{DRM}, T_C = 110 ^{\circ}\text{C}, R_L = 10 \text{ k}) \\ \text{MT2(+)}, G(+); \text{MT2(+)}, G(-); \text{MT2(-)}, G(-) \\ \text{MT2(-)}, G(+) "A" Suffix Only $	Vgт	 0.2 0.2	_ _ _ _	2 2.5 — —	Volts
Holding Current (V _D = 12 Vdc, I _{TM} = 200 mA, Gate Open)	lн	_	_	15	mA
Gate-Controlled Turn-On Time (V _D = Rated V _{DRM} , I _{TM} = 16 A Peak, I _G = 30 mA)	tgt		1.5	_	μѕ
Critical Rate of Rise of Off-State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, T _C = 110°C)	dv/dt	_	25	_	V/μs
Critical Rate of Rise of Commutation Voltage (V _D = Rated V _{DRM} , I _{TM} = 11.3 A, Commutating di/dt = 4.1 A/ms, Gate Unenergized, T _C = 80°C)	dv/dt(c)	_	5	_	V/μs

FIGURE 1 - RMS CURRENT DERATING

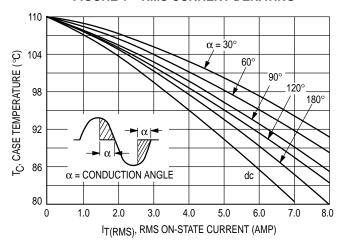
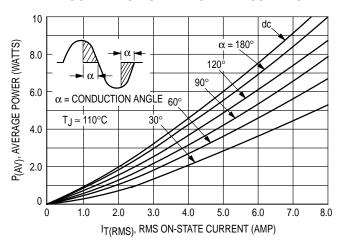
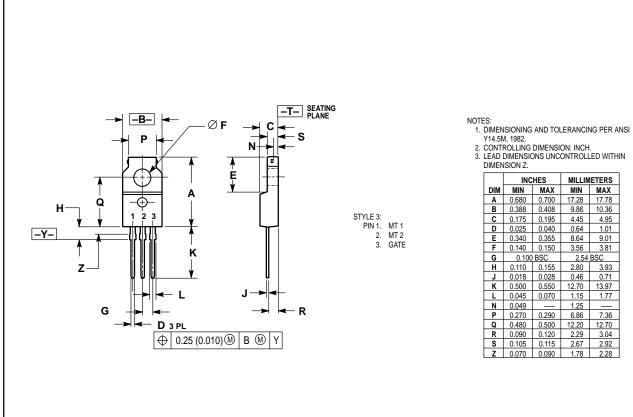


FIGURE 2 - ON-STATE POWER DISSIPATION



PACKAGE DIMENSIONS



	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.680	0.700	17.28	17.78
В	0.388	0.408	9.86	10.36
С	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
Е	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54 BSC	
Н	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049		1.25	
Р	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

CASE 221C-02

MAC228FP Series MAC228AFP Series

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